

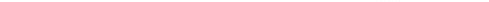
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	09/020,565
				Filing Date	January 16, 1998
				First Named Inventor	Joseph W. Lyding et al.
				Group Art Unit	1763
				Examiner Name	Unknown
Sheet	1	of	2	Attorney Docket Number	22010-128/IL-2-CON

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AUG 03 1998

Examiner Signature		Date Considered	7/21/99
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet

2

of

2

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Lee		GANGULY, Gautam and MATSUDA, Akihisa, "Light-Induced Defect Densities in Hydrogenated and Deuterated Amorphous Silicon Deposited at Different Substrate Temperatures", <u>The Amer. Physical Soc.</u> , Vol. 49, No. 16, pp. 10-986-10 990, (April 15, 1994).	
Lee		MIKKELSEN, J.C., Jr., "Secondary Ion Mass Spectrometry Characterization of D ₂ O and H ₂ ¹⁸ O Steam Oxidation of Silicon", <u>J. of Electronic Matl's</u> , Vol. 11, No. 3, pp. 541-558, (1982).	
Lee		MYERS, S.M. and RICHARDS, P.M., "Interactions of Deuterium With Ion-Irradiated SiO ₂ on Si", <u>J. Appl. Phys.</u> , Vol. 67, No. 9, pp. 4064-4071 (May 1, 1990).	
Lee		PARK, Heungsoo and HELMS, C.R., "The Effect of Annealing Treatment on the Distribution of Deuterium in Silicon and in Silicon/Silicon Oxide Systems", <u>J. Electrochem. Soc.</u> , Vol. 139, No. 7, pp. 2042-2046 (July 1992).	
Lee		SAKS, N.S. and RENDELL, R.W., "The Time-Dependence of Post-Irradiation Interface Trap Build-up in Deuterium-Annealed Oxides", <u>IEEE Transactions on Nuclear Science</u> , Vol. 39, No. 6, pp. 2220-2229 (December 1992).	
Lee		SAKS, N.S. and RENDELL, R.W., "Time-Dependence of the Interface Trap Build-up in Deuterium-Annealed Oxides After Irradiation", <u>Appl. Phys. Lett.</u> , Vol. 61, No. 25, pp. 3014-3016 (December 21, 1992).	
Lee		ZAVADA, J.M., WEISS, B.L., BRADLEY, I.V., THEYS, B., CHEVALLIER, J., RAHBI, R., ADDINALL, R., NEWMAN, R.C. and JENKINSON, H.A., "Optical Waveguides Formed by Deuterium Passivation of Acceptors in Si Doped p-Type GaAs Epilayers", <u>J. Appl. Phys.</u> , Vol. 71, No. 9, pp. 4151-4155 (May 1, 1992).	
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